

**AMENDMENTS TO THE CLAIMS**

1. (Currently amended) A semiconductor device in which one or more semiconductor chips have been mounted onto one or more substrates incorporating patterned wiring and the entirety or entireties of the one or more semiconductor chips has or have been sealed with one or more resins, wherein:

one or more electrically conductive patterns for shielding is or are formed at one or more end faces at the top of at least one of the substrate or substrates.

2. (Original) A semiconductor device according to claim 1 wherein:  
at least one of the electrically conductive pattern or patterns is at least one copper foil pattern.

3. (Original) A semiconductor device according to claim 2 wherein:  
at least one plating having good shielding characteristics is applied over at least one of the copper foil pattern or patterns.

4. (Original) A semiconductor device according to claim 3 wherein:  
at least one of the plating or platings is gold plating.

5. (Previously presented) A semiconductor device according to claim 2 wherein:  
one or more shield cases is or are attached over at least one of the electrically conductive pattern or patterns by way of one or more intervening electrically conductive adhesives.

6. (Original) A semiconductor device according to claim 5 wherein:  
at least one of the shield case or cases is gold-plated.

7. (Previously presented) A semiconductor device according to claim 4 wherein:  
one or more shield cases is or are attached over at least one of the electrically conductive pattern or patterns by way of one or more intervening silver pastes.

8. (Currently amended) A semiconductor device in which one or more semiconductor chips have been mounted onto one or more substrates incorporating patterned wiring and the entirety or entireties of the one or more semiconductor chips has or have been sealed with one or more resins, wherein:

one or more electrically conductive patterns is or are formed at one or more end faces at the bottom of at least one of the substrate or substrates; and

at least as many terminal or terminals of such number, size, and shape as is or are sufficient for connection to the patterned wiring is or are formed by using one or more dies to blank out and shape at least one region at or in the vicinity of at least one of the electrically conductive pattern or patterns.

9. (Original) A semiconductor device according to claim 8 wherein:

at least one of the terminal or terminals is formed so as to at least partially protrude to the exterior and so as to have at least one more or less rectangular cross-section.

10. (Previously presented) A semiconductor device according to claim 8 wherein:

at least one gold plating is applied to at least one end face of at least one of the terminal or terminals.

Claims 11 and 12 (Cancelled).

13. (Previously presented) A semiconductor device according claim 3 wherein:

one or more shield cases is or are attached over at least one of the electrically conductive pattern or patterns by way of one or more intervening electrically conductive adhesives.

14. (Previously presented) A semiconductor device according to claim 4 wherein:

one or more shield cases is or are attached over at least one of the electrically conductive pattern or patterns by way of one or more intervening electrically conductive adhesives.

15. (Previously presented) A semiconductor device according to claim 6 wherein:  
one or more shield cases is or are attached over at least one of the electrically conductive  
pattern or patterns by way of one or more intervening silver pastes.

Claims 16-20 (Cancelled).